

2022 IEEE BiCMOS and Compound Semiconductor Integrated Circuits and Technology Symposium (BCICTS 2022)

**Phoenix, Arizona, USA
16-19 October 2022**



**IEEE Catalog Number: CFP22N20-POD
ISBN: 978-1-6654-9133-4**

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IEEE Catalog Number:	CFP22N20-POD
ISBN (Print-On-Demand):	978-1-6654-9133-4
ISBN (Online):	978-1-6654-9132-7
ISSN:	2831-4972

Additional Copies of This Publication Are Available From:

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